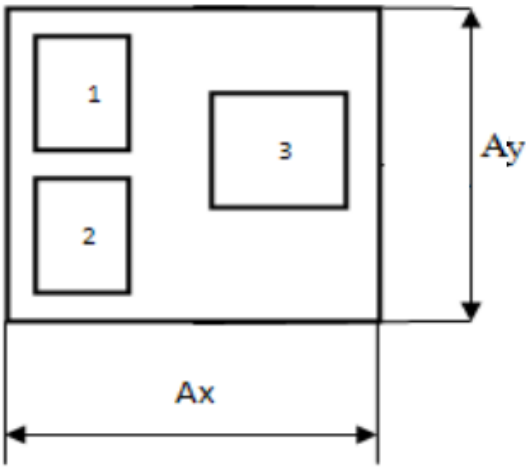

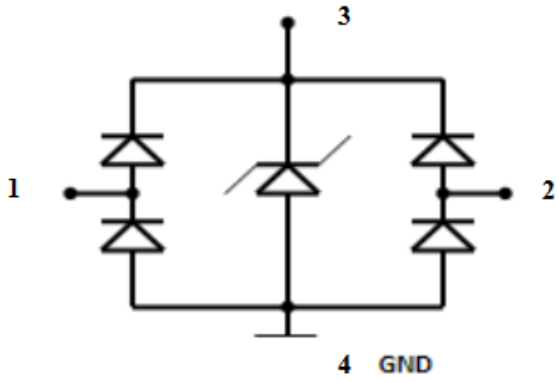

Mechanical data: A_x=380 , A_y=420um
Pad Size: for Pin 1, 2 - 80 *90 um;
for Pin 3 - 140*100 um;
Pin 4 – back side – GND.
Chip thickness: 675 +/-20um.
Scribe Line width - 40um.
Top Metal: Al - for wire bonding.
Back side: Without metallization.
Probing: sampling testing: no bad dice inking; guaranteed good dice quantity≥93%.

Schematic and pinning diagram

Limiting values

Parameter	Symbol	Conditions	Value	Unit
Reverse Stand-off voltage	V_{RWM}	-	5	V
Peak Pulse Power	P_{pp}	t_p= 8/20uS	80*	W
Peak Pulse Current	I_{pp}	t_p= 8/20uS	4*	A
Electrostatic Discharge	V_{ESD}	IEC 61000-4-2, level 4. Contact and Air	>8 (Contact); >15 (Air).	kV
Max.junction temperature	T_j		+125	°C

Characteristics (T_a=25°C)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Breakdown voltage	V_{BR}	IR=1mA. Pin3 to Pin4.	6,1	7,8	8,5	V
Reverse leakage current	I_R	V=5V. Pin 1,2,3 to Pin4	-	-	0,9	uA
Forward voltage	VF	IF=15mA. Pin4 to Pin1,2,3	-	-	1,15	V
Clamping Voltage. Pin 1,2 to Pin4	V_{CL}	Ipp=1.0A, tp=8/20us. Ipp=4,0A, tp=8/20us	-	-	12* 20*	V
Capacitance. Any I/O pin to Ground	C_j	f=1MHz, V_{dc}=0 V.	-	0,6	0,8	pF
Capacitance between I/O pins.	C_j	f=1MHz, V_{dc}=0 V.	-	0,3	0,4	pF

*-For Device testing